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Motion SPM[®] 8 Series

Features

- UL Certified No. E209204 (UL1557)
- 600 V 5 A 3-Phase IGBT Inverter Including Control IC for Gate Drive and Protections
- · Low-Loss, Short-Circuit Rated IGBTs
- Separate Open-Emitter Pins from Low-Side IGBTs for Three-Phase Current Sensing
- Active-high interface, works with 3.3 / 5 V Logic, Schmitt-trigger Input
- HVIC for Gate Driving, Under-Voltage and Short-Circuit Current Protection
- Fault Output for Under-Voltage and Short-Circuit Current Protection
- Inter-Lock Function to Prevent Short-Circuit
- Shut-Down Input
- HVIC Temperature-Sensing Built-In for Temperature Monitoring
- Isolation Rating: 1500 V_{ms} / min.

Applications

Motion Control - Home Appliance / Industrial Motor

Related Resources

• AN-9112 - Smart Power Module, Motion SPM[®] 8 Series User's Guide.



General Description

FNB80560T3 is a Motion SPM 8 module providing a fully-featured, high-performance inverter output stage for AC Induction, BLDC, and PMSM motors. These modules integrate optimized gate drive of the built-in IGBTs to minimize EMI and losses, while also providing multiple on-module protection features including under-voltage lockouts, inter-lock function, over-current shutdown, thermal monitoring of drive IC, and fault reporting. The built-in, high-speed HVIC requires only a single supply voltage and translates the incoming logic-level gate inputs to the high-voltage, high-current drive signals required to properly drive the module's robust short-circuit-rated IGBTs. Separate negative IGBT terminals are available for each phase to support the widest variety of control algorithms.



SPMFA-A25 Figure 1. 3D Package Drawing (Click to Activate 3D Content)

Package Marking and Ordering Information

Device	Device Marking	Package	Packing Type	Quantity
FNB80560T3	NB80560T3	SPMFA-A25	RAIL	15

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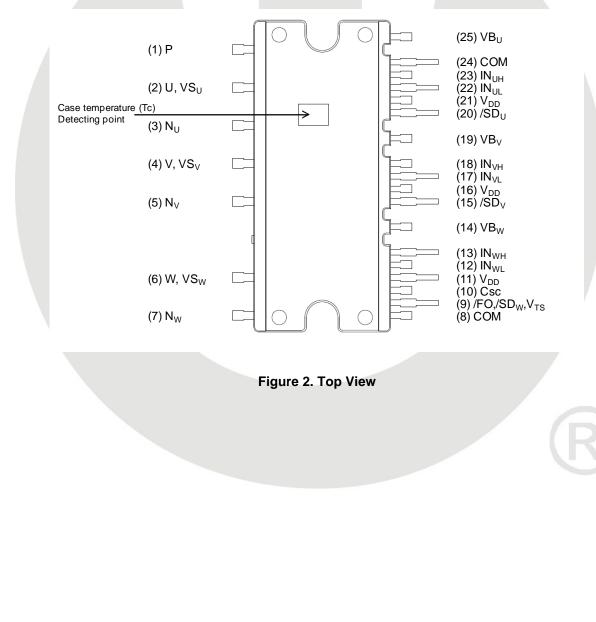
Integrated Power Functions

• 600 V - 5 A IGBT inverter for three phase DC / AC power conversion (Please refer to Figure 3)

Integrated Drive, Protection and System Control Functions

- For inverter high-side IGBTs: gate drive circuit, high-voltage isolated high-speed level shifting
 control circuit Under-Voltage Lock-Out (UVLO) protection
 Note: Available bootstrap circuit example is given in Figures 5 and 17
- control circuit Under-VoltageLock-Out (UVLO) protection
- For inverter low-side IGBTs: gate drive circuit, Over Curent Pretection(OCP), Short-Circuit Protection (SCP) control supply circuit Under-Voltage Lock-Out (UVLO) protection
- · Fault signaling: corresponding to UVLO (low-side supply) and SC faults
- Input interface: High-active interface, woks with 3.3 / 5 V logic, Schmitt trigger input

Pin Configuration



Pin Number	Pin Name	Pin Description	
1	Р	Positive DC-Link Input	
2	U, VS _U	Output for U Phase	
3	NU	Negative DC-Link Input for U Phase	
4	V, VS _V	Output for V Phase	
5	N _V	Negative DC-Link Input for V Phase	
6	W, VS _W	Output for W Phase	
7	N _W	Negative DC-Link Input for W Phase	
8	СОМ	Common Supply Ground	
9	/FO, /SD _W , V_{TS}	Fault Output, Shut-Down Input for W Phase, Temperature Output of Drive IC	
10	C _{SC}	Shut Down Input for Over Current and Short Circuit Protection	
11	V _{DD}	Common Bias Voltage for IC and IGBTs Driving	
12	IN _{WL}	Signal Input for Low-Side W Phase	
13	IN _{WH}	Signal Input for High-Side W Phase	
14	VB _W	High-Side Bias Voltage for W-Phase IGBT Driving	
15	/SD _V	Shut-Down Input for V Phase	
16	V _{DD}	Common Bias Voltage for IC and IGBTs Driving	
17	IN _{VL}	Signal Input for Low-Side V Phase	
18	IN _{VH}	Signal Input for High-Side V Phase	
19	VB _V	High-Side Bias Voltage for V-Phase IGBT Driving	
20	/SD _U	Shut-Down Input for U Phase	
21	V _{DD}	Common Bias Voltage for IC and IGBTs Driving	
22	IN _{UL}	Signal Input for Low-Side U Phase	
23	IN _{UH}	Signal Input for High-Side U Phase	
24	СОМ	Common Supply Ground	
25	VBU	High-Side Bias Voltage for U-Phase IGBT Driving	

Internal Equivalent Circuit and Input/Output Pins Р VBu VB ΗΟ HIN LIN U,VSu vs (<u>v</u>dd V_{DD}-✓/SD_U /SD_U COM LO СОМ Nυ VBv VB ΗΟ HIN τ IN_{VL} V,VSv LIN vs VDD ζ<u>∕sd</u>γ /SD_v LO сом Nv VBv VВ HIN HO LIN ς _{ν_{dd}} W,VSw V_{DD}-VS Csc Csc /FO, /SD_w, V_{TS} LO /FO, /SD_W, V_{TS} COM COM Nw Figure 3. Internal Block Diagram Note: 1. Inverter high-side is composed of three IGBTs, freewheeling diodes. 2. Inverter low-side is composed of three IGBTs, freewheeling diodes. 3. Inverter power side is composed of four inverter DC-link input terminals and three inverter output terminals.

Absolute Maximum Ratings (T_J = 25°C, unless otherwise specified.)

Inverter Part

Symbol	Parameter	Conditions	Rating	Unit	
V _{PN}	Supply Voltage	Applied between P - N _U , N _V , N _W	450	V	
V _{PN(Surge)}	Supply Voltage (Surge)	Applied between P - N _U , N _V , N _W	500	V	
V _{CES}	Collector - Emitter Voltage		600	V	
± I _C	Each IGBT Collector Current	$T_{C} = 25^{\circ}C, T_{J} \le 150^{\circ}C$ (Note 4)	5	А	
$\pm I_{CP}$	Each IGBT Collector Current (Peak)	$T_{C} = 25^{\circ}C, T_{J} \leq 150^{\circ}C, Under 1 ms Pulse$ Width (Note 4)	10	A	
TJ	Operating Junction Temperature		-40 ~ 150	°C	

Control Part

Symbol	Parameter	Conditions	Rating	Unit
V _{DD}	Control Supply Voltage	Applied between V _{DD} - COM	20	V
V _{BS}	High-Side Control Bias Voltage	Applied between VB _U - VS _U , VB _V - VS _V , VB _W - VS _W	20	V
V _{IN}	Input Signal Voltage	Applied between IN _{UH} , IN _{VH} , IN _{WH} , IN _{UL} , IN _{VL} , IN _{VL} , IN _{WL} - COM	-0.3 ~ V _{DD} +0.3	V
V _{FS}	Function Supply Voltage	Applied between /FO, /SD _W ,V _{TS} - COM	-0.3 ~ V _{DD} +0.3	V
I _{FO}	Fault Current	Sink Current at /FO, /SD _W ,V _{TS} pin	2	mA
V _{SC}	Current Sensing Input Voltage	Applied between C _{SC} - COM	-0.3 ~ V _{DD} +0.3	V

Total System

Symbol	Parameter	Conditions	Rating	Unit
V _{PN(PROT)}	Self Protection Supply Voltage Limit (Short Circuit Protection Capability)	$V_{DD} = V_{BS} = 13.5 \sim 16.5$ V, $T_{J} = 150^{\circ}$ C, Non-Repetitive, < 2 μ s	400	V
Т _С	Module Case Operation Temperature	See Figure 2	-40 ~ 125	°C
T _{STG}	Storage Temperature		-40 ~ 125	°C
V _{ISO}	Isolation Voltage Connect Pins to Heat Sink Plate	AC 60 Hz, Sinusoidal, 1 Minute, Connection Pins to Heat Sink Plate	1500	V _{rms}

Thermal Resistance

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
11(-0)0	Junction to Case Thermal Resistance	Inverter IGBT part, (Per Module)	-	-	3.60	°C / W
R _{th(j-c)F}	(Note 5)	Inverter FWDi part, (Per Module)	-	-	4.03	°C / W

Note:

4. These values had been made an acquisition by the calculation considered to design factor.

5. For the measurement point of case temperature (T $_{\mbox{C}}$), please refer to Figure 2.

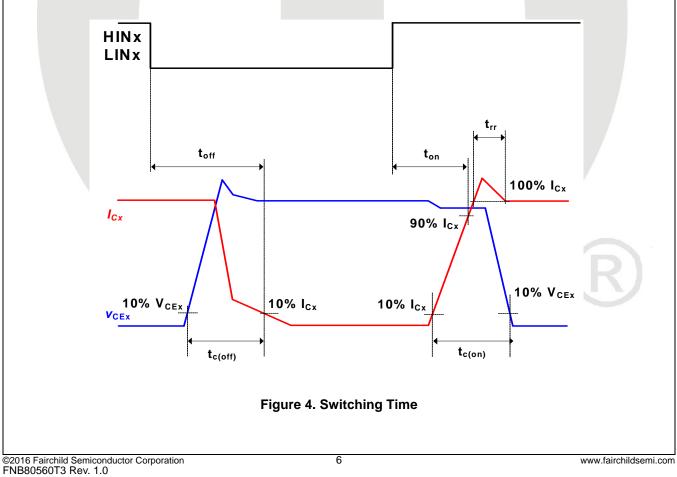
Electrical Characteristics ($T_J = 25^{\circ}C$, unless otherwise specified.)

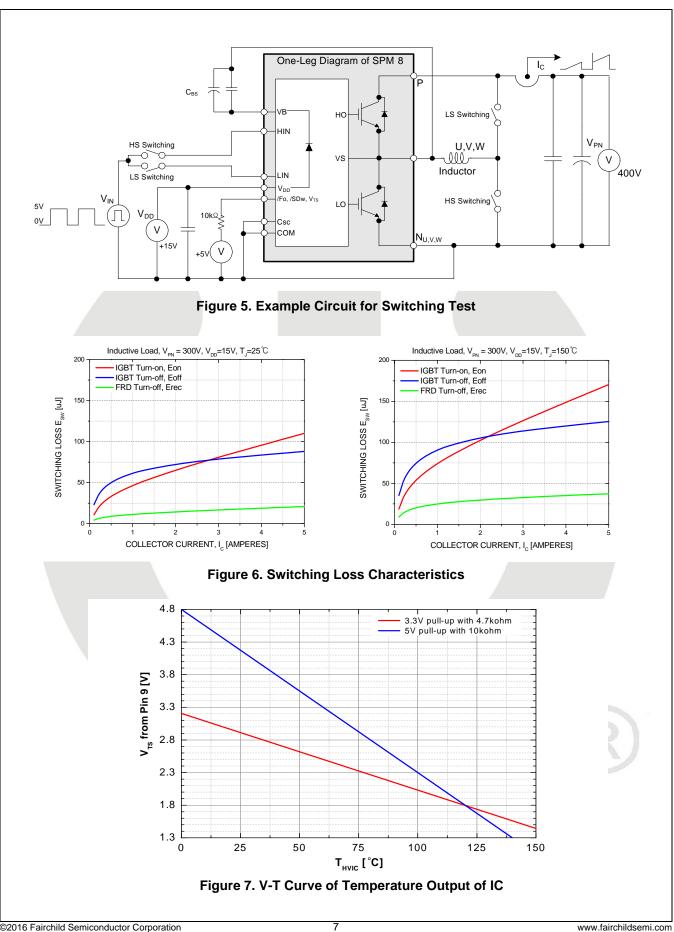
Inverter Part

S	ymbol	Parameter	Cond	litions	Min.	Тур.	Max.	Unit
V _{CE(SAT)}		Collector - Emitter Saturation Voltage	$V_{IN} = 5 V$	$T_J = 25^{\circ}C$	-	1.75	2.25	V
			$I_{\rm C} = 4 {\rm A}$	$T_J = 150^{\circ}C$	-	2.00	-	V
	V _F	FWDi Forward Voltage	V _{IN} = 0 V	$T_J = 25^{\circ}C$	-	1.90	2.50	V
			I _F = 4 A	T _J = 150°C	-	1.80	-	V
HS	t _{ON}	Switching Times	$V_{PN} = 400 \text{ V}, \text{ V}_{DD} = \text{ V}$	_{BS} = 15 V, I _C = 5A	0.30	0.70	1.10	us
	t _{C(ON)}		$T_J = 25^{\circ}C$ $V_{IN} = 0 V \leftrightarrow 5 V$, Indu	ctive load	-	0.15	0.45	us
	t _{OFF}		(Note 6) $(\text{Note } 6)$		-	0.50	1.00	us
	t _{C(OFF)}				-	0.10	0.40	us
	t _{rr}				-	0.10	-	us
LS	t _{ON}		$V_{PN} = 400 \text{ V}, V_{DD} = V$	r _{BS} = 15 V, I _C = 5A	0.30	0.70	1.10	us
	t _{C(ON)}		$T_J = 25^{\circ}C$ $V_{IN} = 0 V \leftrightarrow 5 V$, Indu	ctive load	-	0.15	0.45	us
	t _{OFF}		(Note 6) $($ Note 6)		-	0.50	1.00	us
	t _{C(OFF)}				-	0.10	0.40	us
	t _{rr}				- /	0.10	-	us
	I _{CES}	Collector - Emitter Leakage Current	V _{CE} = V _{CES}		-	-	1.00	mA

Note:

t_{ON} and t_{OFF} include the propagation delay of the internal drive IC. t_{C(ON)} and t_{C(OFF)} are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Figure 4.



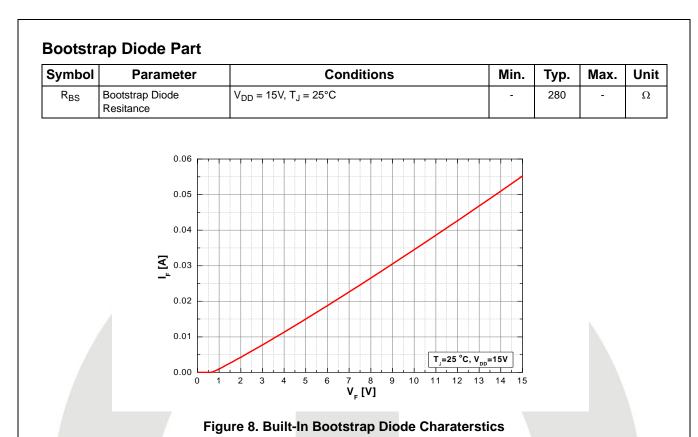


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Symbol	nbol Parameter Conditions			Min.	Тур.	Max.	Uni
I _{QDD}	Quiescent V _{DD} Supply Current	V _{DD} = 15 V, IN _(UH,VH,WH,UL,VL,WL) = 0 V	_D - COM	-	-	1.7	mA
I _{PDD}	Operating V _{DD} Supply Current	V_{DD} = 15 V, f_{PWM} = 20 kHz, duty = V_{DI} 50%, applied to one PWM signal input	_D - COM	-	-	2.0	mA
I _{QBS}	Quiescent V _{BS} Supply Current		(U) - V _{S(U)} , V _{B(V)} - (V), V _{B(W)} - V _{S(W)}	-	-	100	μA
I _{PBS}	Operating V _{BS} Supply Current		(U) - V _{S(U)} , V _{B(V)} - (V), V _{B(W)} - V _{S(W)}	-	-	500	μA
V _{FOH}	Fault Output Voltage	V_{SC} = 0 V, V_F Circuit: 10 k Ω to 5 V Pull-	-up	3.81	-	-	V
V _{FOL}		V_{SC} = 1 V, V_F Circuit: 10 k Ω to 5 V Pull-up		-	-	0.5	V
V _{SC(ref)}	Short-Circuit Trip Level	V _{DD} = 15 V (Note 7)		0.46	0.49	0.52	V
UV _{DDD}		Detection level		10.0	11.5	13.0	V
UV_DDR	Supply Circuit Under-Voltage	Reset level		10.5	12.0	13.5	V
UV _{BSD}	Protection	Detection level		9.5	11.0	12.5	V
UV _{BSR}		Reset level		10.0	11.5	13.0	V
I _{FO_T}	HVIC Temperature	$V_{DD} = V_{BS} = 15$ V, $T_{HVIC} = 25^{\circ}C$		-	82.5	-	μΑ
	Sensing Current	$V_{DD} = V_{BS} = 15$ V, $T_{HVIC} = 75^{\circ}C$		-	207.5	-	μA
V _{FO_T}	HVIC Temperature	$V_{DD} = V_{BS} = 15$ V, $T_{HVIC} = 25^{\circ}$ C, 10 k Ω	to 5 V Pull-up	-	4.18	-	V
	Sensing Voltage See Figure 7	$V_{DD} = V_{BS} = 15 \text{ V}, \text{ T}_{HVIC} = 75^{\circ}\text{C}, 10 \text{ k}\Omega$	to 5 V Pull-up	-	2.93	-	V
t _{FOD}	Fault-Out Pulse Width			40	-	-	μS
V _{FSDR}	Shut-down Reset level	Applied between /FO - COM		-	-	2.4	V
V _{FSDD}	Shut-down Detection level			0.8	-	-	V
V _{IN(ON)}	ON Threshold Voltage	Applied between IN(UH), IN(VH), IN(WH	_{H)} , IN _(UL) , IN _(VL) ,	-	-	2.4	V
V _{IN(OFF)}	OFF Threshold Voltage	IN _(WL) - COM		0.8	-	-	V

7. Short-circuit current protection function is for all six IGBTs if the /FO, /SD_W, V_{TS} pin is connected to /SD_x pins.

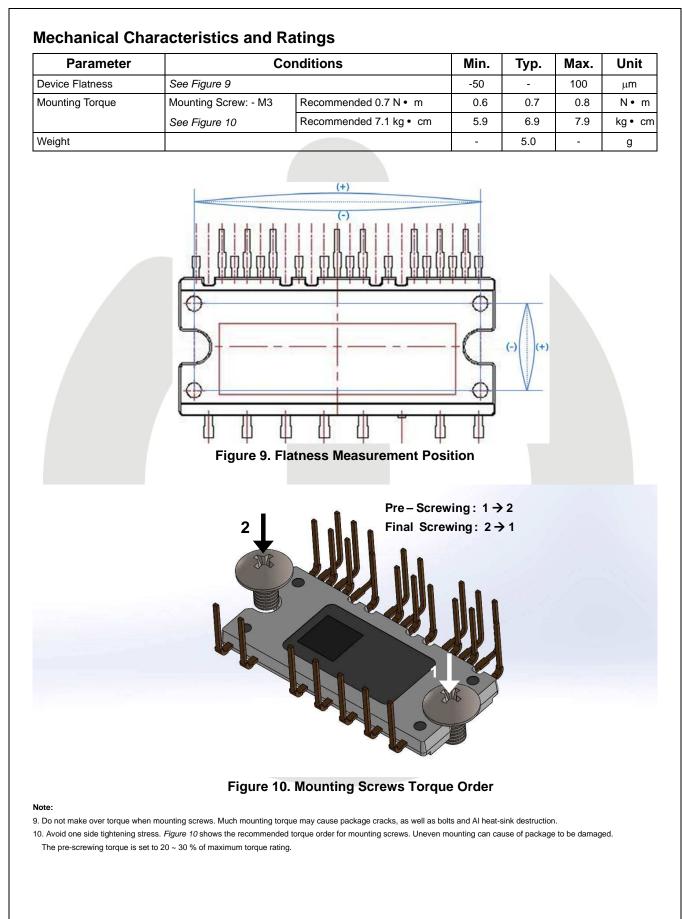


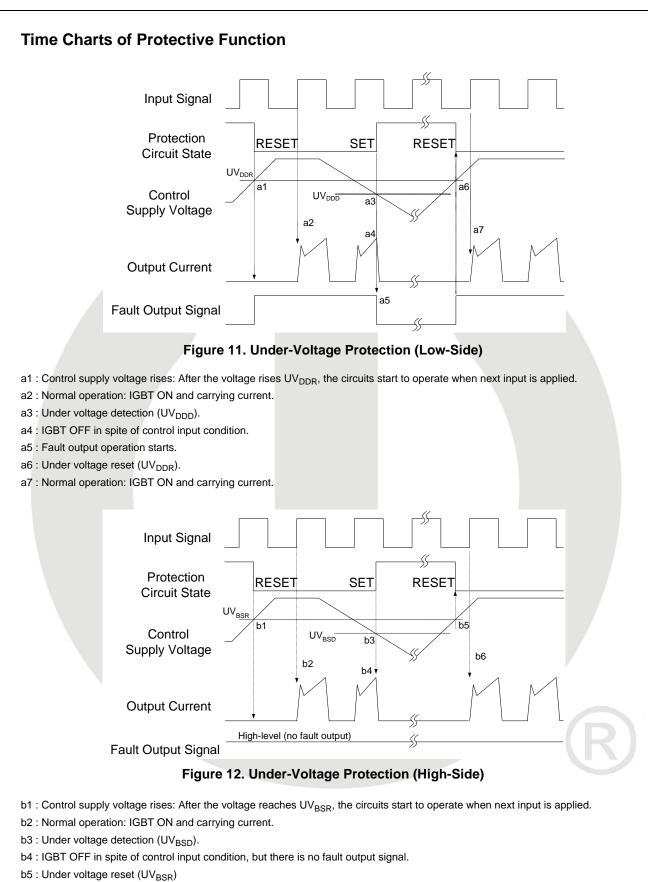
Recommended Operating Conditions

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V _{PN}	Supply Voltage	Applied between P - N _U , N _V , N _W	-	300	400	V
V _{DD}	Control Supply Voltage	Applied between V _{DD} - COM	14.0	15	16.5	V
V _{BS}	High - Side Bias Voltage	Applied between $VB_U - VS_U$, $VB_V - VS_V$, $VB_W - VS_W$	13.0	15	18.5	V
dV _{DD} / dt, dV _{BS} / dt	Control Supply Variation		-1	-	1	V / μs
t _{dead}	Blanking Time for Preventing Arm - Short	For each input signal		-	-	μs
V _{SEN}	Voltage for Current Sensing	Applied between N _U , N _V , N _W - COM (Including surge voltage)	-4		4	V
P _{WIN(ON)}	Minimun Input Pulse	V_{DD} = V_{BS} = 15 V, I_C \leq 10 A, Wiring Inductance	0.7	-	<u> </u>	μS
P _{WIN(OFF)}	Width	between $N_{U, V, W}$ and DC Link N < 10nH (Note 7)	0.7	- /	-	

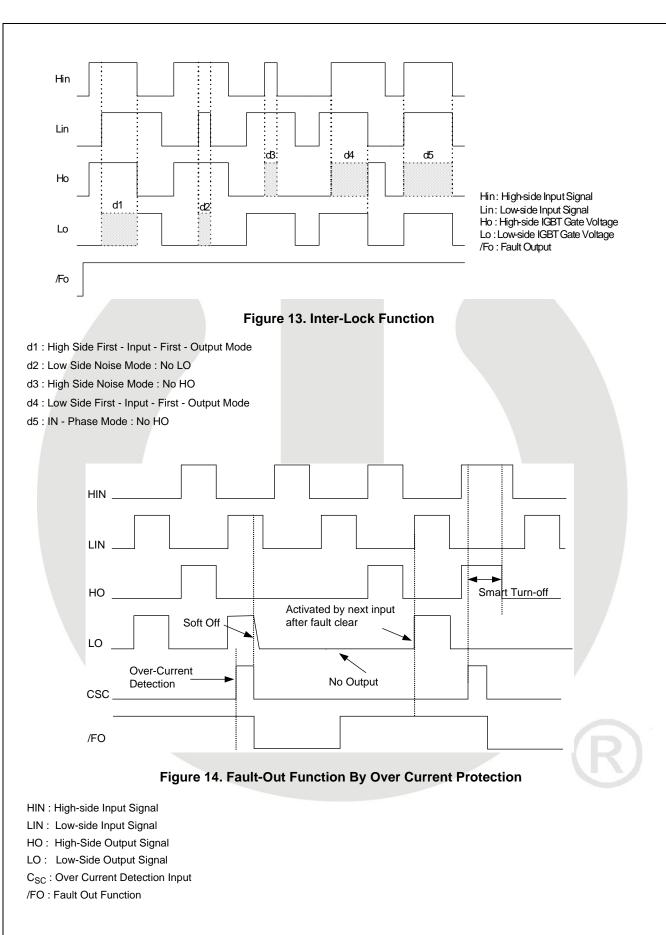
Note:

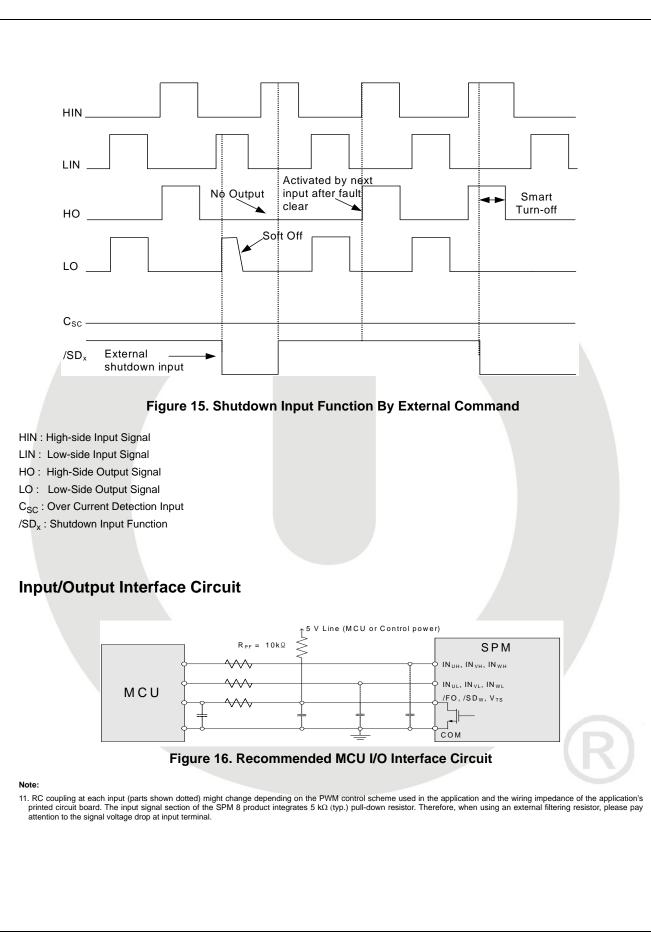
8. This product might not make response if input pulse width is less than the recommanded value.

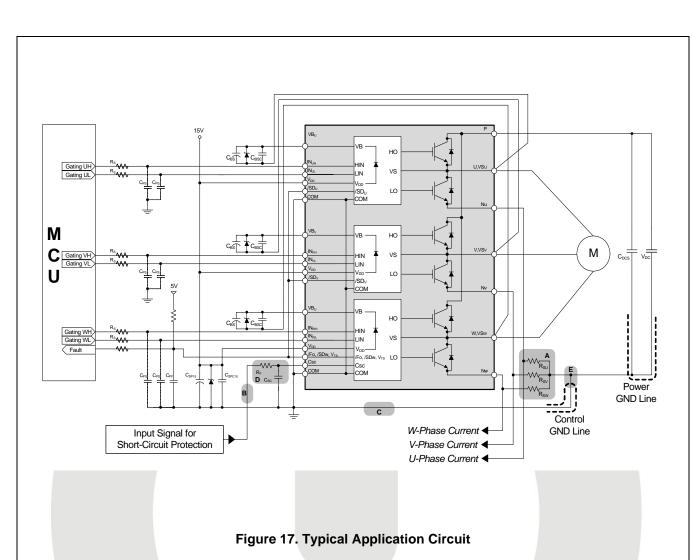




b6 : Normal operation: IGBT ON and carrying current

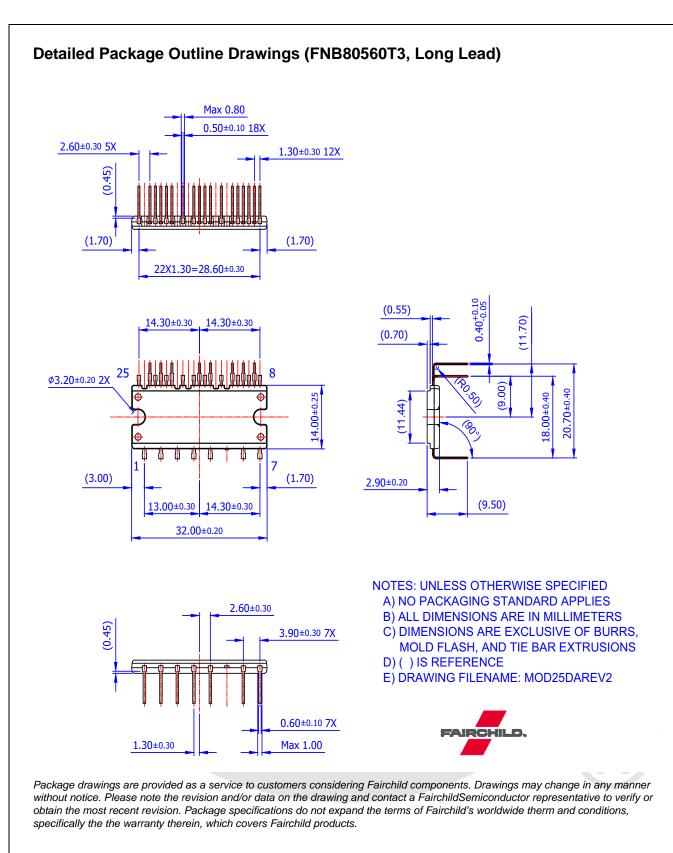






Note:

- 12. To avoid malfunction, the wiring of each input should be as short as possible. (less than 2 ~ 3 cm)
- 13. /FO is open-drain type. This signal line should be pulled up to the positive side of the MCU or control power supply with a resistor that makes I_{FO} up to 2 mA. *Please refer to Figure 16.*
- 14. C_{SP15} of around seven times larger than bootstrap capacitor C_{BS} is recommended.
- 15. Input signal is active-HIGH type. There is a 5 kΩ resistor inside the IC to pull down each input signal line to GND. RC coupling circuits is recommanded for the prevention of input signal oscillation. R_SC_{PS} time constant should be selected in the range 50 ~ 150 ns. (Recommended R_S = 100 Ω, C_{PS} = 1 nF)
- 16. Each wiring pattern inductance of A point should be minimized (Recommend less than 10nH). Use the shunt resistor R_{S(UV/W)} of surface mounted (SMD) type to reduce wiring inductance. To prevent malfunction, wiring of point E should be connected to the terminal of the shunt resistor R_{S(UV/W)} as close as possible.
- 17. To prevent errors of the protection function, the wiring of B, C, and D point should be as short as possible.
- 18. In the short-circuit protection circuit, please select the R_FC_{SC} time constant in the range 1.5 ~ 2 μs. Do enough evaluation on the real system because short-circuit protection time may very wiring pattern layout and value of the R_F and C_{SC} time constant.
- 19. The connection between control GND line and power GND line which includes the N_U, N_V, N_W must be connected to only one point. Please do not connect the control GND to the power GND by the broad pattern. Also, the wiring distance between control GND and power GND should be as short as possible.
- 20. Each capacitor should be mounted as close to the pins of the Motion SPM 8 product as possible.
- 21. To prevent surge destruction, the wiring between the smoothing capacitor and the P and GND pins should be as short as possible. The use of a high frequency non-inductive capacitor of around 0.1 ~ 0.22 μF between the P and GND pins is recommended.
- 22. Relays are used at almost every systems of electrical equipments of home appliances. In these cases, there should be sufficient distance between the CPU and the relays.
- 23. The zener diode or transient voltage suppressor should be adopted for the protection of ICs from the surge destruction between each pair of control supply terminals. (Recommanded zener diode is 22 V / 1 W, which has the lower zener impedance characteristic than about 15 Ω)
- 24. Please choose the electrolytic capacitor with good temperature characteristic in C_{BS}. Also, choose 0.1 ~ 0.2 µF R-category ceramic capacitors with good temperature and frequency characteristics in C_{BSC}.
- 25. For the detailed information, please refer to the application notes.
- 26. /FO and /SD must be connected as short as possible.



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http://www.fairchildsemi.com/dwg/MO/MOD25DA.pdf

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